

Features

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

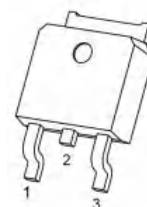
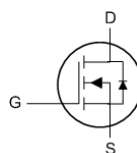
Application

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Power Management in Telecom., Industrial Automation, CE

V_{DS} 100 V
 I_D 120 A
 $R_{DS(ON)}$ 3.5m Ω



LOGO GK XXX CODE
120 N 10
ID VDSS



Schematic Diagram TO-263(G:1 D:2 S:3)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Pulsed Drain Current ⁽²⁾	I_{DM}	689	A
Avalanche Energy ⁽³⁾	E_{AS}	726	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 100^\circ\text{C}$	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$			1.0	μA
		$T_J = 55^{\circ}\text{C}$			5.0	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	3.0	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		3.5	4.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 20\text{A}$		50		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.66	1.0	V
Diode Continuous Current	I_S	$T_C = 25^{\circ}\text{C}$			215	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$		4797		pF
Output Capacitance	C_{oss}			900		pF
Reverse Transfer Capacitance	C_{rss}			19.1		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		1.9		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 20\text{A}$		84		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			57		nC
Gate Source Charge	Q_{gs}			24		nC
Gate Drain Charge	Q_{gd}			27		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$ $R_L = 2.5\Omega$, $R_{GEN} = 3\Omega$		21		ns
Turn-On Rise Time	t_r			35		ns
Turn-Off DelayTime	$t_{D(off)}$			49		ns
Turn-Off Fall Time	t_f			30		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		71		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		127		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.40	0.60	$^{\circ}\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^{\circ}\text{C}$.
3. E_{AS} of 726 mJ is based on starting $T_J = 25^{\circ}\text{C}$, $L = 3\text{mH}$, $I_{AS} = 22\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$; 100% test at $L = 0.3\text{mH}$, $I_{AS} = 45\text{A}$.
 $T_{J_Max} = 150^{\circ}\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^{\circ}\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

RATING AND CHARACTERISTIC CURVES

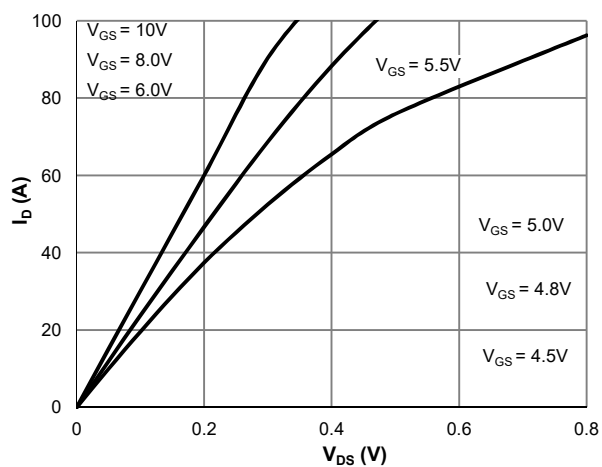


Figure 1: Saturation Characteristics

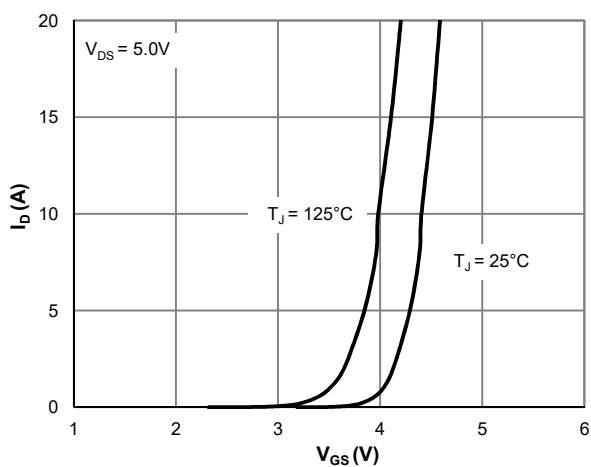


Figure 2: Transfer Characteristics

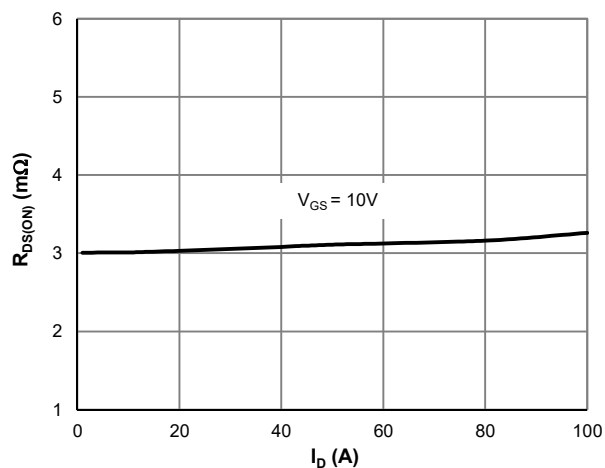


Figure 3: $R_{DS(ON)}$ vs. Drain Current

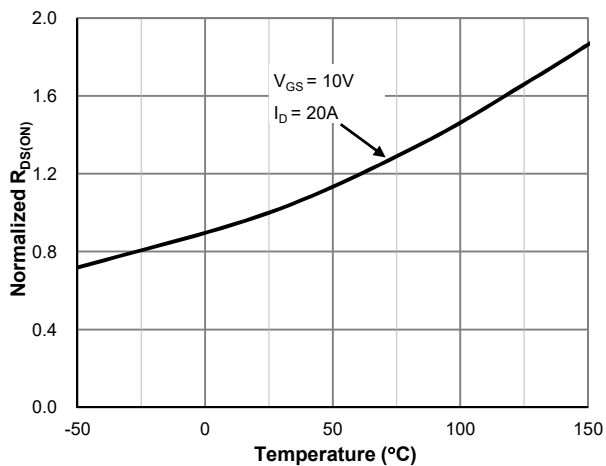


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

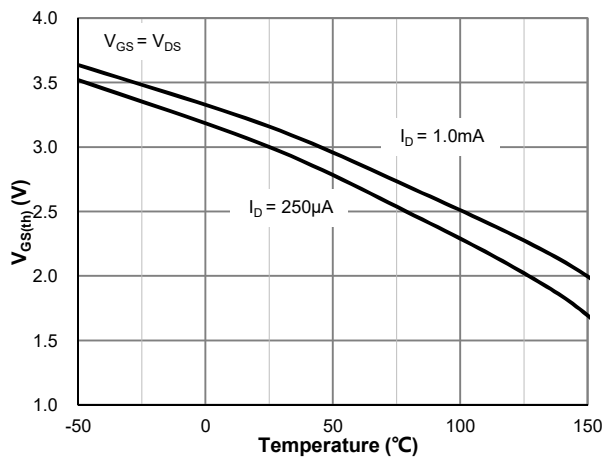


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

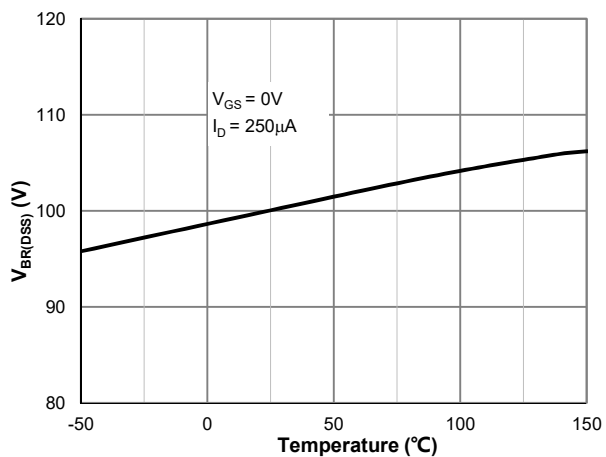


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

RATING AND CHARACTERISTIC CURVES

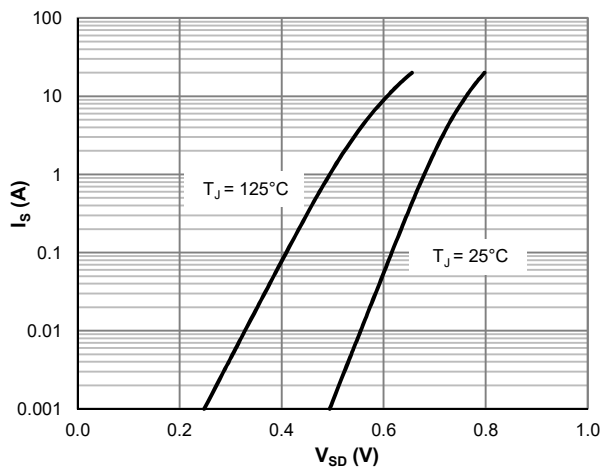


Figure 7: Body-Diode Characteristics

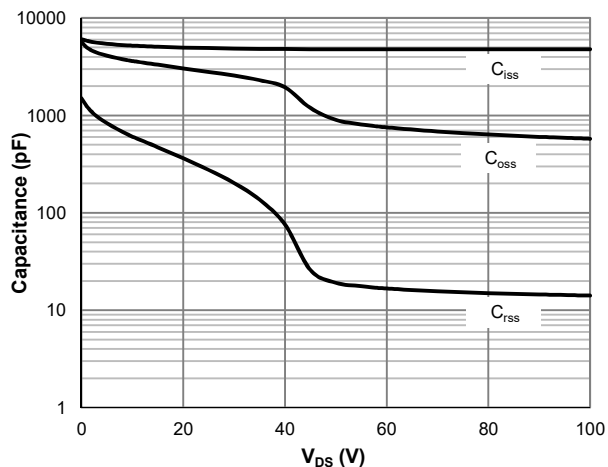


Figure 8: Capacitance Characteristics

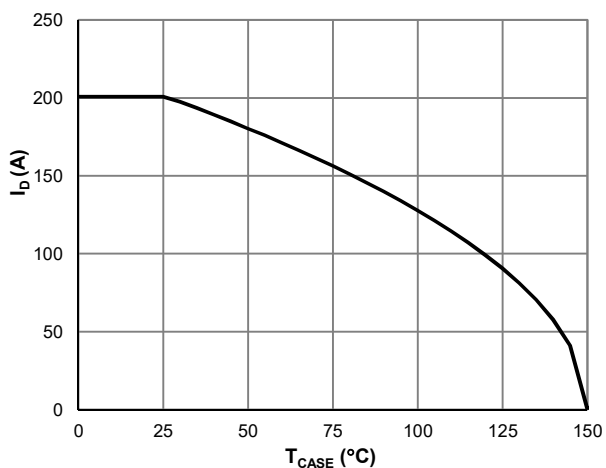


Figure 9: Current De-rating

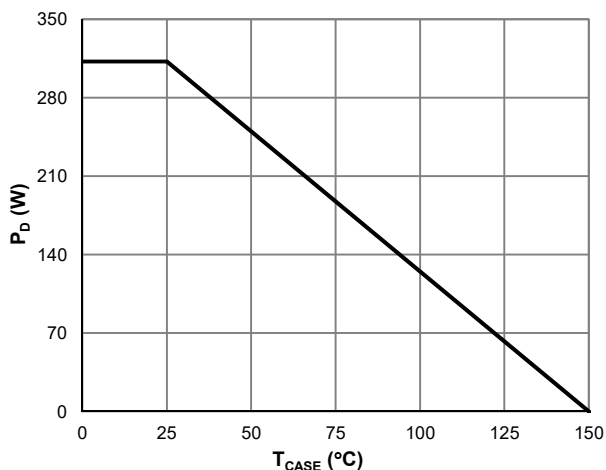


Figure 10: Power De-rating

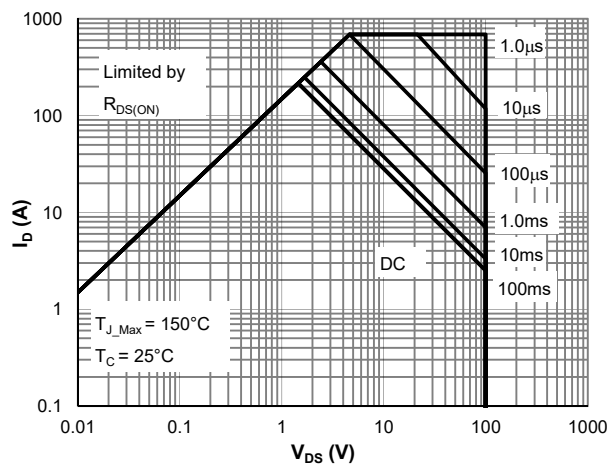
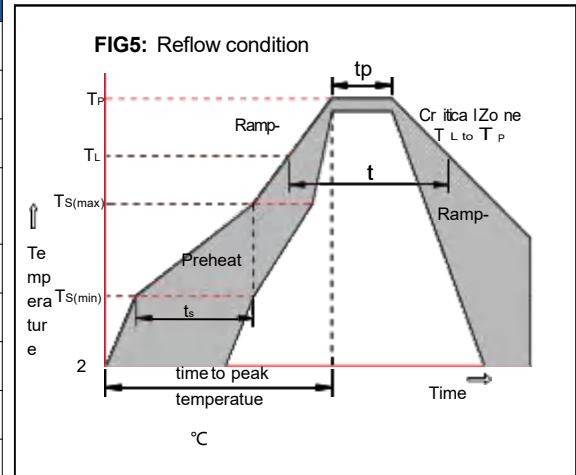


Figure 11: Maximum Safe Operating Area

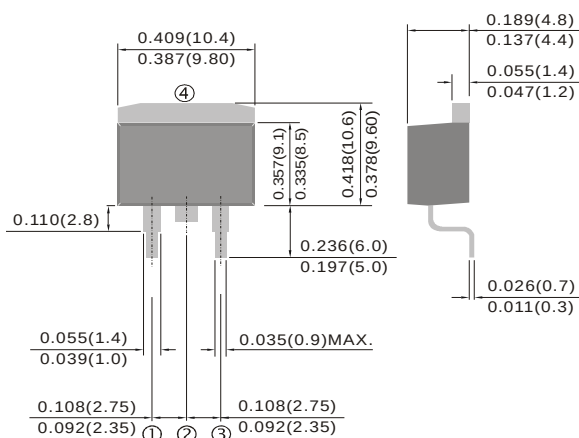
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

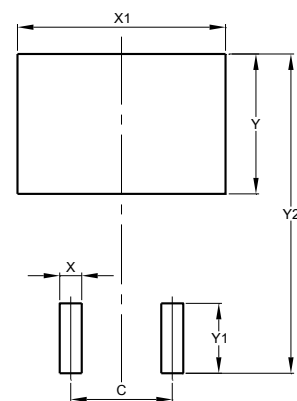


Package Dimensions & Suggested Pad Layout

TO-263 / D²PAK



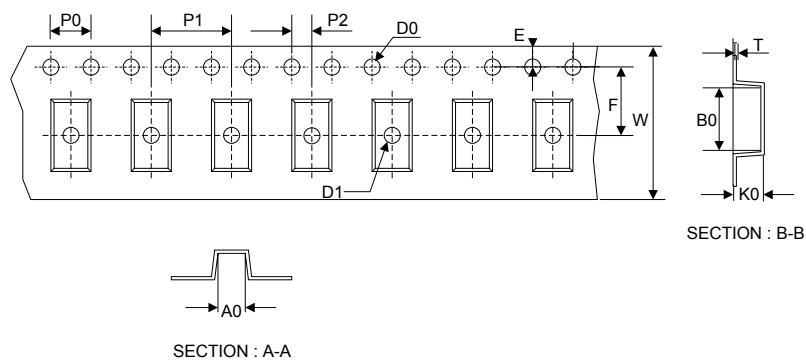
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	5.05
X	1.40
X1	11.00
Y	9.20
Y1	4.00
Y2	16.60

Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	16.00±0.20
P2	2.00±0.20
D0	1.50±0.20
D1	1.50±0.20
E	1.75±0.15
F	11.50±0.20
W	24.00±0.40
A0	10.50±0.20
B0	16.00±0.25
K0	5.20±0.25
T	0.35±0.10
D2	330.0±5.0
D3	73Min.
D4	14.0±2.5
W1	28.00±2.0
Quantity: 800PCS	

13" Reel

